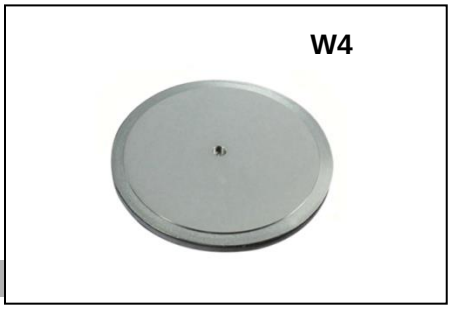
高端电力电子器件和装置制造商

ZP13500 - 焊接二极管

200-400 V_{DRM}

焊 接 二 极 管

特 性：
* 扩散工艺
* 大电流特性
* 低压降
* 陶瓷管壳封装
* 极低热阻值



电 学 特 性 值

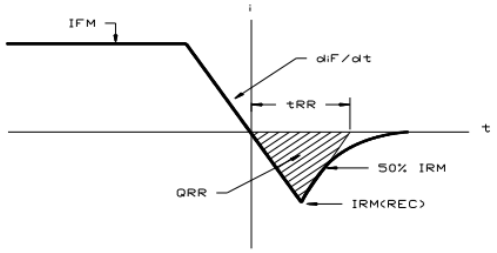
Reverse Blocking

Device Type	V_{RRM} (1)	V_{RSM} (1)
ZP13500 -02	200	300
ZP13500 -04	400	450

V_{RRM} = Repetitive peak reverse voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I_{RRM}	10 mA 75 mA (3)

Notes:
All ratings are specified for Tj=25 ºC, unless otherwise stated .
(1) Sine half wave, f=50Hz, Tj = -40 to +180ºC.
(2) Sine half wave, Pulse width 10 msec. Tj = -40 to +180ºC.
(3) Maximum value for Tj = 180 ºC.
(4) See parameter definition below :



REVERSE RECOVERY CHARACTERISTIC

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	$I_{F(AV)}$		13500		A	Sinewave 180º, Tc =85℃
RMS forward current	I_{FRMS}		21200		A	
Peak one cycle surge (non repetitive) current	I_{FSM}		85000		A	Pulse width 10 msec, sinusoidal wave-shape, 180º conduction, Tj = 180 ℃
I square t	I^2t		36100		KA^2s	Pulse width 10 msec, sinusoidal wave-shape, Tj = 180 ℃
Peak forward voltage	V_{FM}		0.97		V	I_{FM}= 5000A; 25℃
Threshold voltage	V_{TO}		0.76		V	Tj = 180 ℃
Slope resistance	r_T		0.021		mΩ	Tj = 180 ℃
Reverse Recovery Current (4)	$I_{RM(REC)}$				A	I_{FM} = 1000 A; dIF/dt = 10 A/µs;Tjmax
Reverse Recovery Charge (4)	Q_{rr}				µC	I_{FM} = 1000 A; dIF/dt = 10 A/µs;Tjmax
Reverse Recovery Time (4)	t_{rr}				µs	I_{FM} = 1000 A; dIF/dt = 10 A/µs;Tjmax

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+180		°C	
Storage temperature	T_{stg}	-40	+180		°C	
Thermal resistance - junction to case	$R_{\Theta (j-c)}$		0.0039		°C/W	Double sided cooled
Thermal resistance - junction to case	$R_{\Theta (j-c)}$		0.026		°C/W	Single sided cooled
Creepage distance	D_S		2		mm	
Air breakdown distance	D_a		2		mm	
Mounting force	F	35	40	35	kN	
Weight	W			140	g	

* Mounting surfaces smooth, flat and greaseless

外形图